

a source region and a drain region each including a first impurity;

a channel forming region being formed between the source region and the drain region; and

an impurity region including a second impurity having an opposite conductive type to the first impurity and being formed under the channel forming region and in the source region,

wherein the impurity region is not in contact with the drain region, and

wherein a concentration of the second impurity in the channel forming region is from 1/100 to 1/10 of that in the impurity region formed under the channel forming region and in the source region.

29. (Fourth Amendment) A semiconductor device comprising a plurality of MOSFETs formed in a single crystal semiconductor substrate,

each of the plurality of MOSFETs comprising:

a source region and a drain region each including a first impurity;

a channel forming region being formed between the source region and the drain region;

an impurity region including a second impurity having an opposite conductive type to the first impurity and being

formed under the channel forming region and in the source region;

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a pair of LDD regions, wherein one of the pair of LDD regions is formed between the source region and the channel forming region while the other of the pair of LDD regions is formed between the channel forming region and the drain region,

wherein the impurity region is not in contact with the drain region, and

wherein a concentration of the second impurity in the channel forming region is from 1/100 to 1/10 of that in the impurity region formed under the channel forming region and in the source region.

42. (Fourth Amendment) A semiconductor device comprising at least a CMOS circuit including an n-channel MOSFET and a p-channel MOSFET each being formed in a single crystal semiconductor substrate,

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said n-channel MOSFET comprising:

a first source region and a first drain region each comprising a first n-type impurity;

a first channel forming region being formed between the first source region and the first drain region;

a first impurity region including a first p-type impurity and being formed under the first channel forming region and in the first source region;

wherein the first impurity region is not in contact with the drain region,

said p-channel MOSFET comprising:

a second source region and a second drain region each comprising a second p-type impurity;

a second channel forming region being formed between the second source region and the second drain region;

a second impurity region including a second n-type impurity and being formed under the second channel forming region.

56. (First Amendment) An EL display device comprising:

a plurality of MOSFETs formed in a single crystal semiconductor substrate, each of the plurality of MOSFETs comprising:

a source region and a drain region each including a first impurity;

a channel forming region being formed between the source region and the drain region; and

an impurity region including a second impurity having an opposite conductive type to the first impurity and being formed under the channel forming region and in the source region,

wherein the impurity region is not in contact with the drain region,

wherein a concentration of the second impurity in the channel forming region is from 1/100 to 1/10 of that in the impurity region,

wherein the second impurity is introduced from a direction of the $\langle 110 \rangle$ axis with respect to the single crystal semiconductor substrate, so that the second impurity is introduced from a perpendicular direction to a plane having the smallest atomic density of the single crystal semiconductor substrate,

wherein the concentration of the second impurity in the impurity region is in a range of 1×10^{18} to 1×10^{19} atoms/cm³,

wherein the concentration of the second impurity in the channel forming region is in a range of 1×10^{16} to 1×10^{17} atoms/cm³.

57. (First Amendment) An EL display device according to claim 56,

wherein the first n-type impurity is arsenic,

wherein the second n-type impurity is phosphorus, and

wherein each of the first and second p-type impurities is
boron.

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